ECE 532 Writing Assignment – Spring 2015

Novel Monolithic Doherty Power Amplifier Topologies in GaN

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***Abstract* – The use of carbon nanotubes**

I. Introduction

Give some background on Doherty amp. For example explain very high level how it works. And why it is useful or a good amp

This paper is organized as follows. Section II explores the DPA and some of its disadvantages. Section III explores novel DPA topologies that increase efficiency and bandwidth.

II. Doherty Amplifier

III. Doherty Amplifier Topologies

Write some kind of intro here

1. Reconfigurable Matching Networks

For proper operation of the DPA the inputs of the carrier and peaking amplifiers must be 90° out of phase. 90° phase shift is realized with a λ/4 transformer ether in micro strip or lumped element depending on the operating frequency. It is obvious that this presents a challenge if large bandwidth is desired. To solve this problem reconfigurable input and output matching networks (IMN/OMN) are proposed. Figure 1 shows a schematic of a reconfigurable DPA.

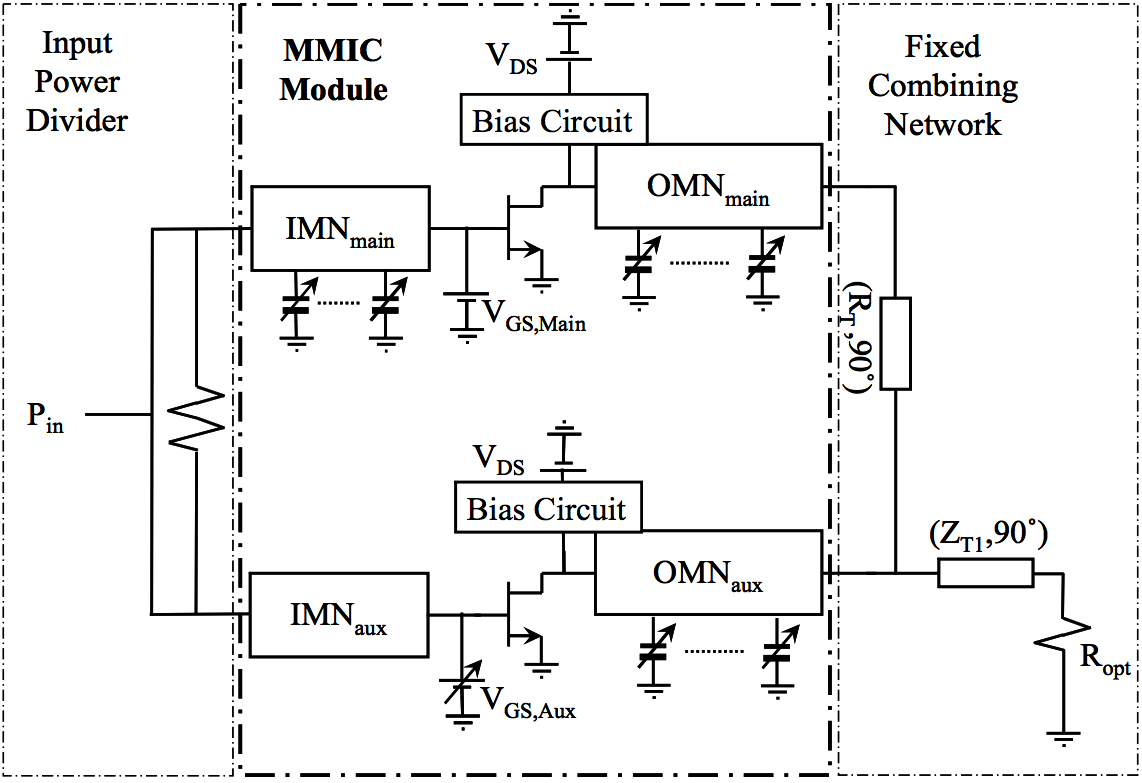


Figure 1 Schematic of Reconfigurable DPA [1]

To achieve reconfigurable matching networks microelectromechanical systems (MEMS) are used. MEMS devices are preferred due to their ultra-linearity, low losses, and easy of integration in current MMIC processes [1]. A reconfigurable matching network can present the optimum impedances to both input and output of the transistor for the best gain and efficiency at various operating frequencies. As shown in [1] such topology yielded high power gains and efficiency at 1.7, 2.14 and 2.6 GHz using the same amplifier with reconfigurable matching networks.

1. Class F amplifier in Peaking branch
2. Raymonds section
3. another section maybe? driver stage

IV. Conclusion

In this paper we explored some of the

References

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[3] P. Colantonio, F. Giannini, R. Giofre, and L. Piazzon, “Efficiency improvement in Doherty power amplifier by using Class F approach,” in 2009 European Microwave Integrated Circuits Conference (EuMIC), 28-29 Sept. 2009, 2009, pp. 17–20.

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